

N-channel 100 V 7.6 mΩ standard level MOSFET in D2PAK 18 December 2012 Product data sheet

### 1. General description

Standard level N-channel MOSFET in a D2PAK package qualified to 175 °C. Part of Nexperia's "NextPower Live" portfolio, the PSMN7R6-100BSE complements the latest "hot-swap" controllers - robust enough to withstand substantial inrush currents during turn on, whilst offering a low  $R_{DS(on)}$  characteristic to keep temperatures down and efficiency up in continued use. Ideal for telecommunication systems based on a 48 V backplane / supply rail.

### 2. Features and benefits

- Enhanced forward biased safe operating area for superior linear mode operation
- Very low R<sub>DS(on)</sub> for low conduction losses

### 3. Applications

**T**. I. I. A

- Electronic fuse
- Hot swap
- Load switch
- Soft start

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### 4. Quick reference data

1.1.1

	ick reference data				_		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	100	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	-	75	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	296	W
Static charac	teristics	-					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 12		-	6.5	7.6	mΩ
Dynamic cha	racteristics						
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V;		-	41	-	nC
Q <sub>G(tot)</sub>	total gate charge	<u>Fig. 14; Fig. 15</u>		-	128	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Avalanche Ruggedness							
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$V_{GS}$ = 10 V; T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 75 A; V <sub>sup</sub> ≤ 100 V; R <sub>GS</sub> = 50 Ω; unclamped; Fig. 3		-	-	426	mJ

[1] Continuous current limited by package

### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain[1]		
3	S	source		G-UF44
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

[1] It is not possible to make connection to pin 2

### 6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PSMN7R6-100BSE	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404				

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN7R6-100BSE	PSMN7R6100BSE

### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	М	lin	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-		100	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-		100	V
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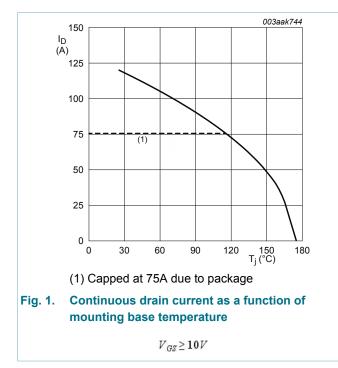
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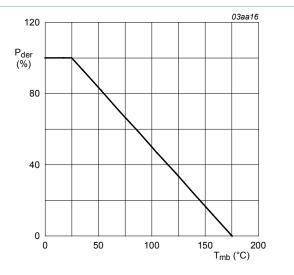
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Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	75	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 1</u>	[1]	-	75	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 4		-	481	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	296	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drai	in diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	75	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$		-	481	А
Avalanche F	Ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}\text{C}; \; I_{D} = 75 \; \text{A}; \\ V_{sup} \leq 100 \; V; \; R_{GS} = 50 \; \Omega; \; unclamped; \\ \hline \text{Fig. 3} \end{array}$		-	426	mJ

[1] Continuous current limited by package





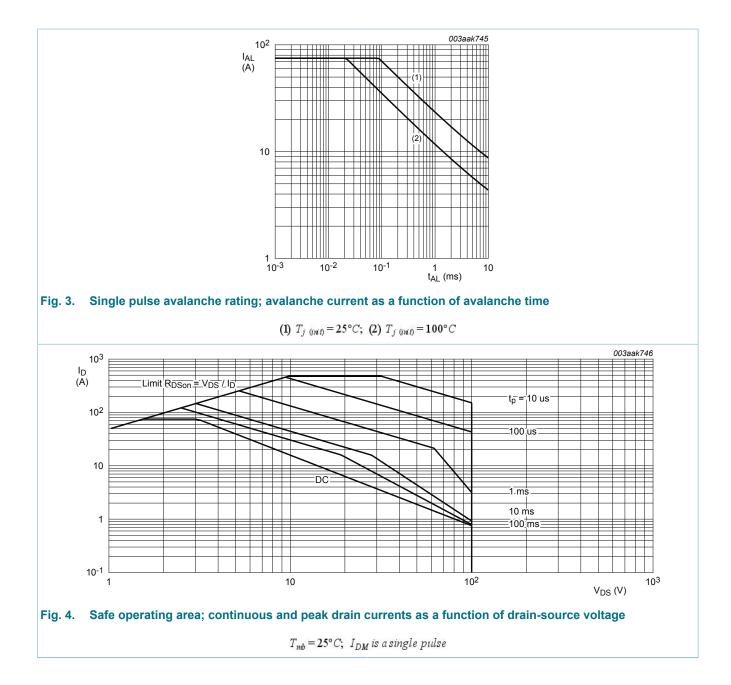


$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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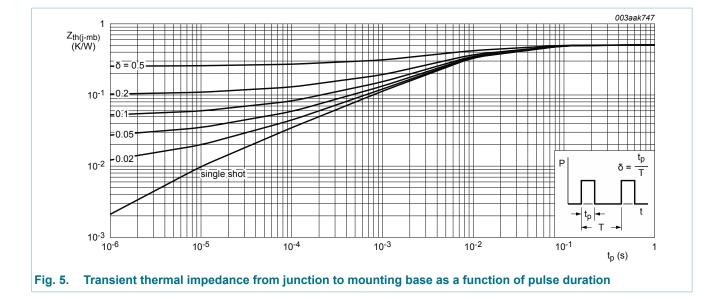
### 9. Thermal characteristics

Table 6. The	rmal characteristics		 			
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	0.42	0.51	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W

#### Table 6. Thermal characteristic

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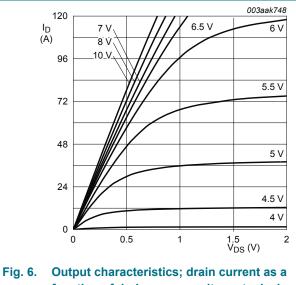
### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · ·				
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	100	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	90	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; Fig. 10; Fig. 11	2	3	4	V
V <sub>GSth</sub> gate-source thresh voltage	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 11	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 11	-	-	4.6	V
I <sub>DSS</sub> drain lea	drain leakage current	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.1	2	μA
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
		$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 12	-	6.5	7.6	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C; Fig. 12; Fig. 13	-	-	13.7	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 13	-	-	20.5	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	0.42	0.83	1.66	Ω

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Dynamic cl	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; Fig. 14; Fig. 15	-	128	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	110	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D$ = 25 A; $V_{DS}$ = 50 V; $V_{GS}$ = 10 V;	-	33	-	nC
Q <sub>GD</sub>	gate-drain charge	Fig. 14; Fig. 15	-	41	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	5.3	-	V
C <sub>iss</sub>	input capacitance	$V_{DS}$ = 50 V; $V_{GS}$ = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	7110	-	pF
C <sub>oss</sub>	output capacitance		-	450	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	310	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 50 V; R <sub>L</sub> = 2 Ω; V <sub>GS</sub> = 10 V;	-	31	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	48	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	82	-	ns
t <sub>f</sub>	fall time		-	47	-	ns
Source-dra	in diode	· ·	I	1		
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 17</u>	-	0.8	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{\rm S}$ = 25 A; dI_{\rm S}/dt = -100 A/µs; V <sub>GS</sub> = 0 V;	-	69	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 50 V	-	210	-	nC





 $T_j = 25^{\circ}C$ 

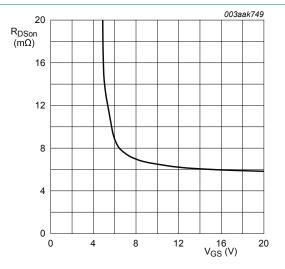


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

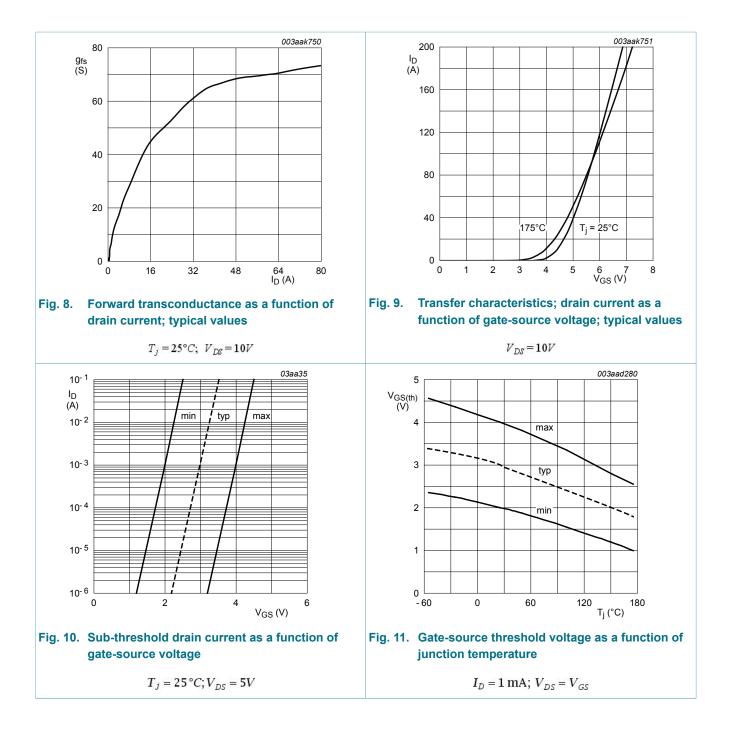
 $T_j = 25^{\circ}C; \ I_D = 25A$ 

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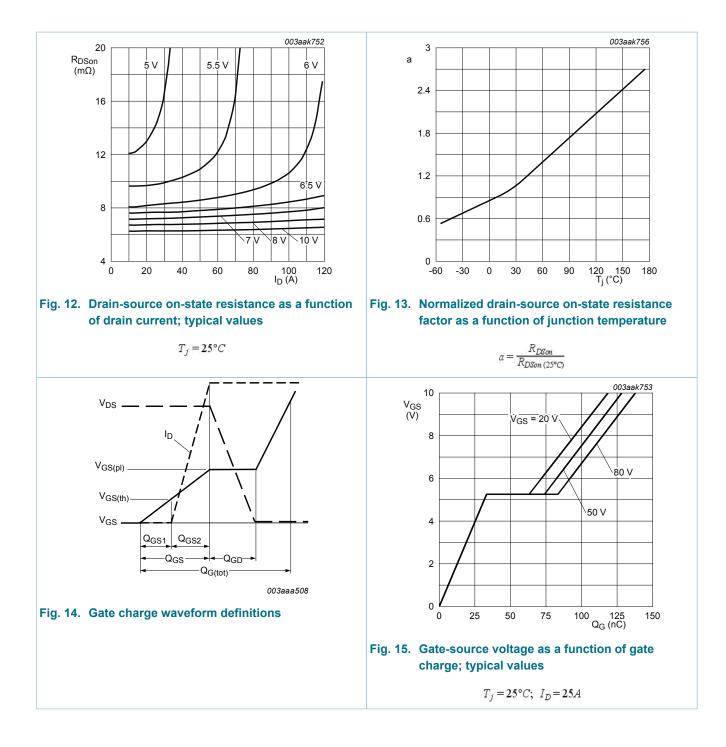
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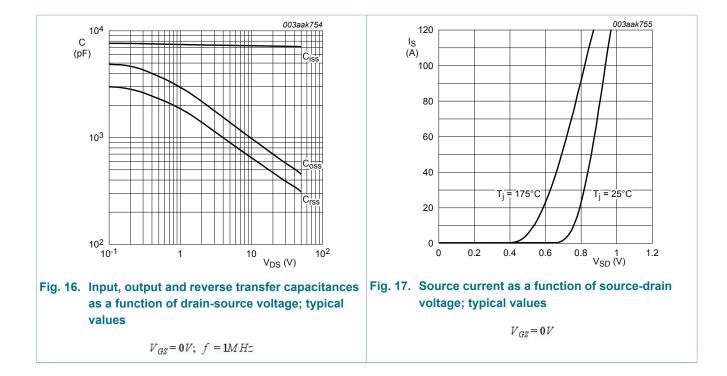
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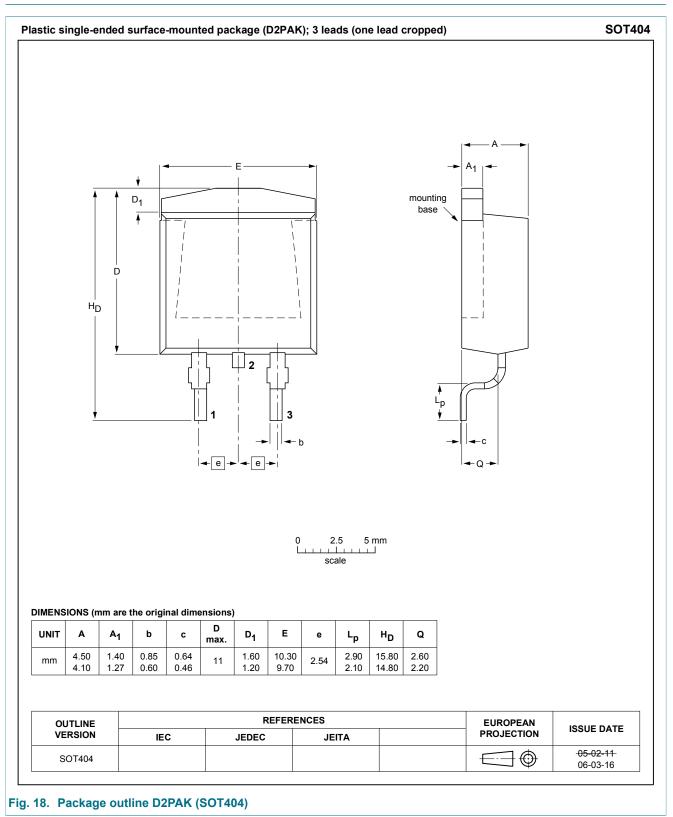
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#### N-channel 100 V 7.6 mΩ standard level MOSFET in D2PAK

### 11. Package outline



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#### N-channel 100 V 7.6 mΩ standard level MOSFET in D2PAK

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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